

File View Edit Tools Window Help

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 L1: (1730) KRAM

 L2: (295) L1 and (second near3 magnetic near3 layer)

 L3: (11) L2 and (dummy near3 cell)

☐ Failed

☒ Saved

 (135369) memory and magnetic

 (5) (memory and magnetic) and ((first and second) with (magnetic adj3

 (15) (memory and magnetic) and (magnetic adj3 layer) and (insulat\$3 ne

 (161) (memory adj2 cell) and (insulat\$3 near3 film) and (magnet\$8 near

 (161) (memory adj2 cell) and (magnet magnetic) and (insulat\$3 near3 f

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DBs: USPAT, US POPUS, EPO, JPO, DERIVENT, BM, TOR

Default operator: OR

☐ Check

☐ Highlight all hits immediately

		Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C						
1	<input type="checkbox"/>	US 2003030935 A1	20030515	48	Thin film magnetic memory device for programming	365/171			Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	US 2003031455 A1	20030501	39	Thin film magnetic memory device having data read	365/173	365/158; 365/171;		Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	US 20030031046 A1	20030213	29	Thin film magnetic memory device realizing both	365/171			Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	US 20030031045 A1	20030213	19	Magnetic random access memory including memory cell	365/158			Hosotani, Keiji	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	US 20030026125 A1	20030206	72	Thin film magnetic memory device including memory	365/158			Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	US 20020172073 A1	20021121	69	Thin film magnetic memory device capable of conducting	365/158			Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
7	<input type="checkbox"/>	US 20020172068 A1	20021121	59	Thin film magnetic memory device having a magnetic	365/100			Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

L Number	Hits	Search Text	DB	Time stamp
1	1730	MRAM	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/24 17:08
2	295	MRAM and (second near3 magnetic near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/24 17:09
3	11	(MRAM and (second near3 magnetic near3 layer)) and (dummy near3 cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/24 17:09
-	135369	memory and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 11:43
-	5	(memory and magnetic) and ((first and second) with (magnetic adj3 layer)) and (insulat\$3 near3 film) and (reference near3 voltage) and (dummy near3 cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 11:52
-	15	(memory and magnetic) and (magnetic adj3 layer) and (insulat\$3 near3 film) and (reference near3 voltage) and (dummy near3 cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 12:05
-	161	(memory adj2 cell) and (insulat\$3 near3 film) and (magnet\$8 near3 direction) and (magnet\$8 near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 12:08
-	161	(memory adj2 cell) and (magnet magnetic) and (insulat\$3 near3 film) and (magnet\$8 near3 direction) and (magnet\$8 near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 12:08